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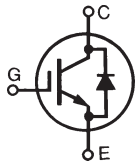
IXYS

XPT™ 600V IGBTs GenX3™ w/ Diode

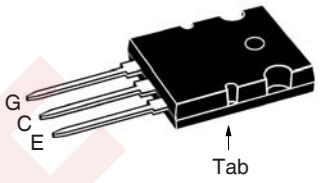
IXXK100N60C3H1
IXXX100N60C3H1

V_{CES} = 600V
I_{C90} = 100A
$V_{CE(sat)}$ ≤ 2.20V
$t_{fi(typ)}$ = 75ns

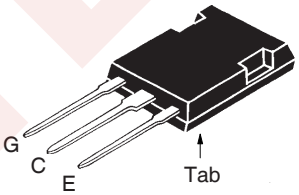
Extreme Light Punch Through
IGBT for 20-60kHz Switching



TO-264 (IXXK)



PLUS247 (IXXX)



G = Gate E = Emitter
C = Collector Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	170	A
I_{LRMS}	Terminal Current Limit	120	A
I_{C90}	T_C = 90°C	100	A
I_{F110}	T_C = 110°C	65	A
I_{CM}	T_C = 25°C, 1ms	340	A
I_A	T_C = 25°C	50	A
E_{AS}	T_C = 25°C	600	mJ
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 2Ω Clamped Inductive Load	I_{CM} = 200 @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	V_{GE} = 15V, V_{CE} = 360V, T_J = 150°C R_G = 10Ω, Non Repetitive	10	µs
P_C	T_C = 25°C	695	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264 PLUS247	10 6	g g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250µA, V_{GE} = 0V	600			V
$V_{GE(th)}$	I_C = 250µA, V_{CE} = V_{GE}	3.0		5.5	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	µA
	T_J = 125°C			4	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 70A, V_{GE} = 15V, Note 1		1.68	2.20	V
	T_J = 150°C		1.97		V

Features

- International Standard Packages
- Optimized for 20-60kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

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Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	22	40		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		4810		pF
C_{oes}			455		pF
C_{res}			80		pF
$Q_{g(on)}$	I_C = 70A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		150		nC
Q_{ge}			34		nC
Q_{gc}			60		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		30		ns
t_{ri}	I_C = 70A, V_{GE} = 15V		70		ns
E_{on}	V_{CE} = 360V, R_G = 2Ω		2.00		mJ
$t_{d(off)}$	Note 2		90		ns
t_{fi}			75		ns
E_{off}			0.95	1.40	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		30		ns
t_{ri}	I_C = 70A, V_{GE} = 15V		65		ns
E_{on}	V_{CE} = 360V, R_G = 2Ω		3.00		mJ
$t_{d(off)}$	Note 2		105		ns
t_{fi}			115		ns
E_{off}			1.40		mJ
R_{thJC}				0.18	°C/W
R_{thCS}			0.15		°C/W

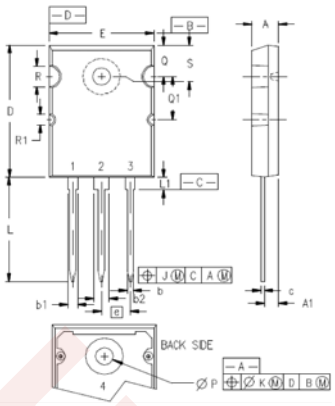
Reverse Diode (FRED)

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 60A, V_{GE} = 0V, Note 1		1.6	2.0	V
	T_J = 150°C		1.4	1.8	V
I_{RM}	I_F = 60A, V_{GE} = 0V, T_J = 100°C		8.3		A
t_{rr}	$-di_F/dt$ = 200A/µs, V_R = 300V		140		ns
R_{thJC}				0.30	°C/W

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

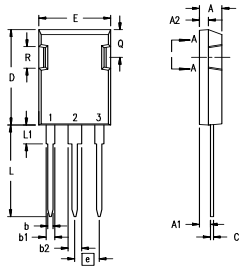
TO-264 Outline



Terminals: 1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ Outline



Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

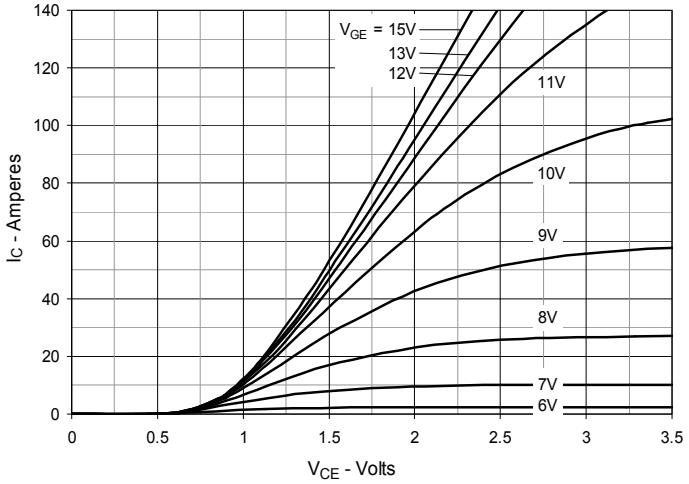


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

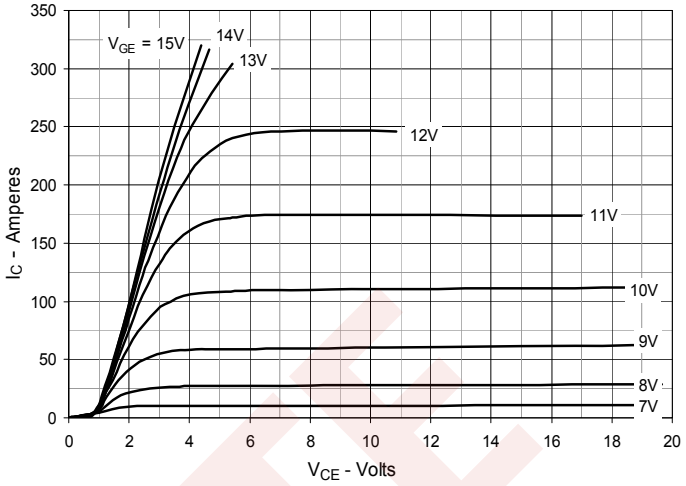


Fig. 3. Output Characteristics @ T_J = 150ºC

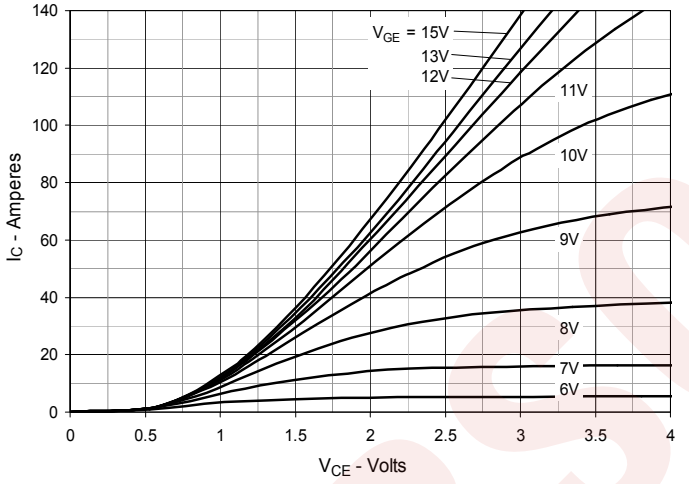


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

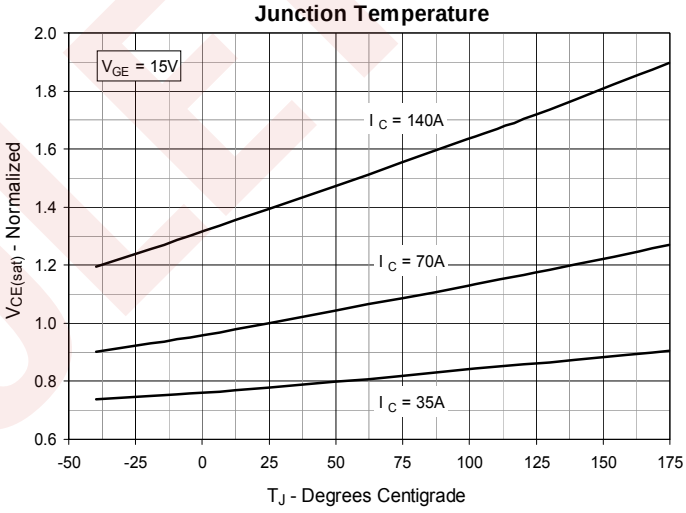


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

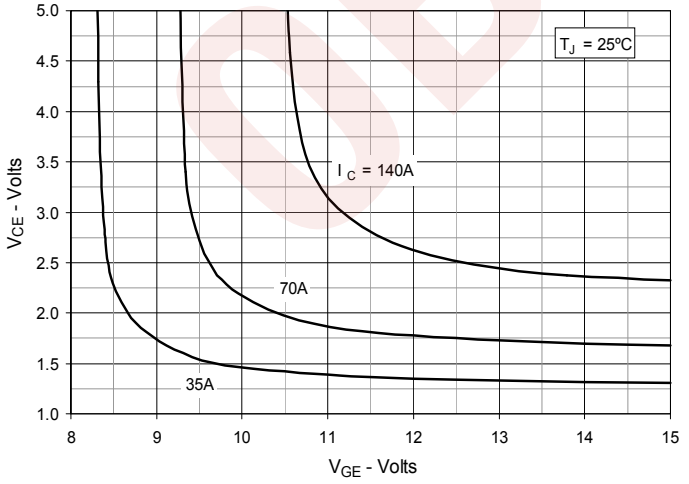
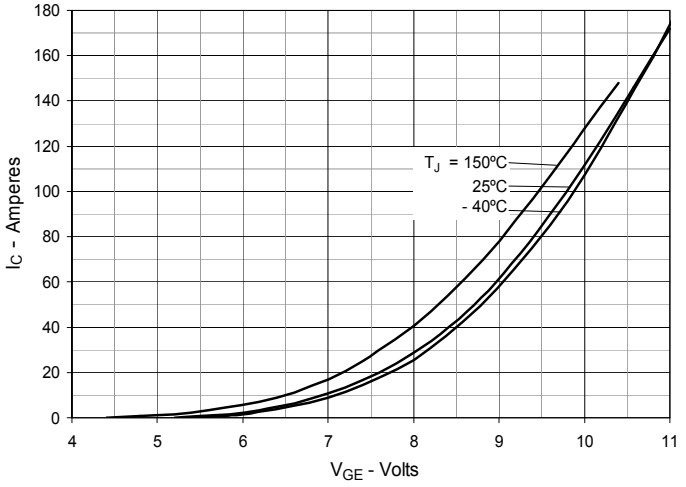


Fig. 6. Input Admittance



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Fig. 7. Transconductance

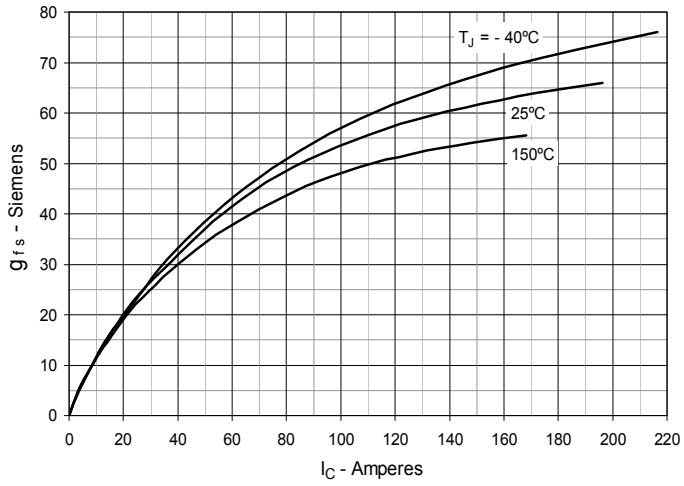


Fig. 8. Gate Charge

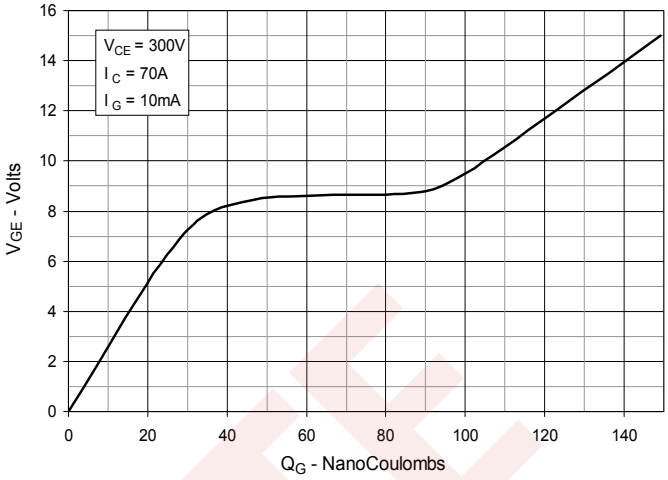


Fig. 9. Capacitance

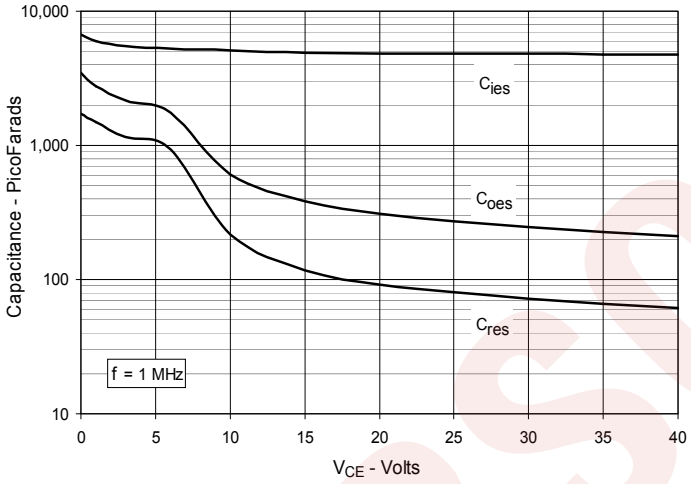


Fig. 10. Reverse-Bias Safe Operating Area

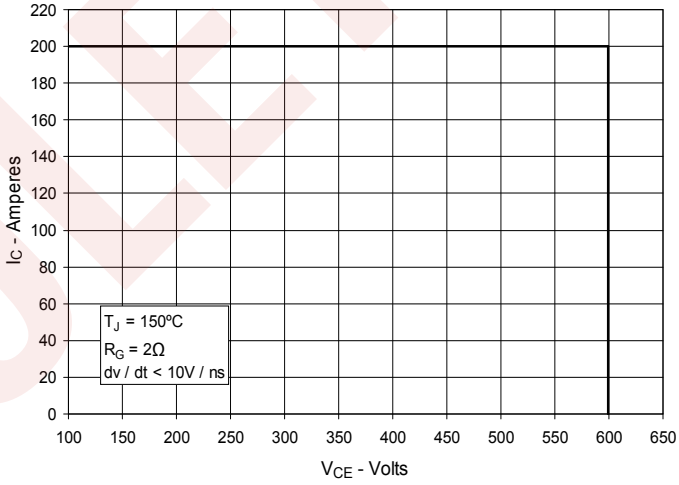


Fig. 11. Forward-Bias Safe Operating Area

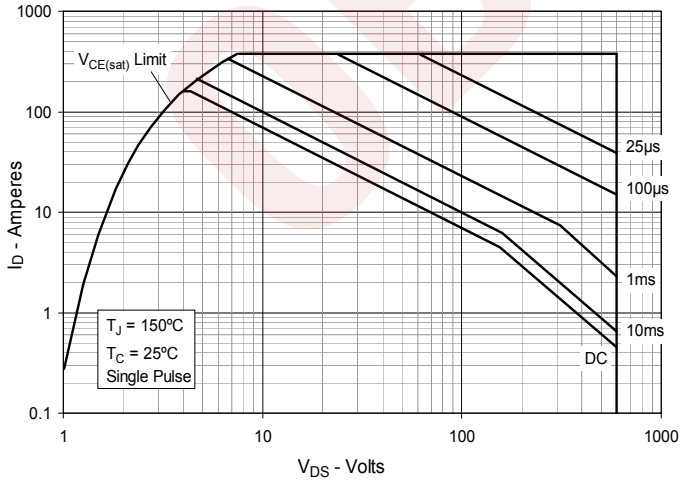
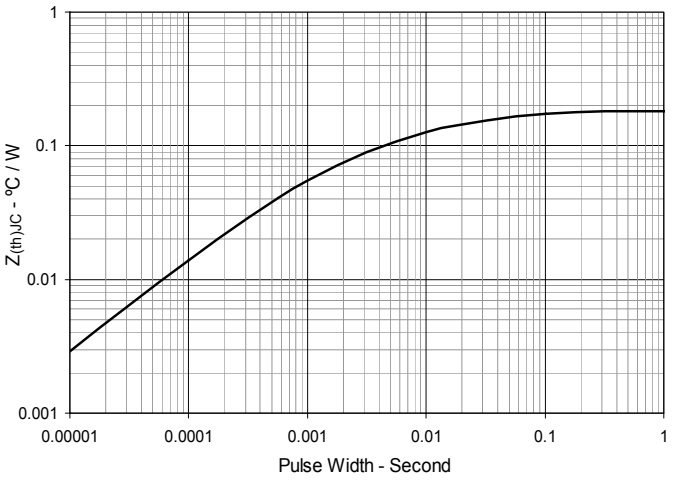


Fig. 12. Maximum Transient Thermal Impedance



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Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

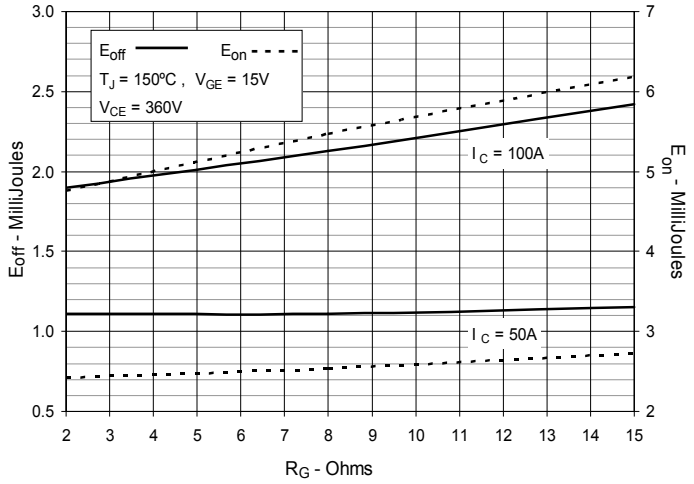


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

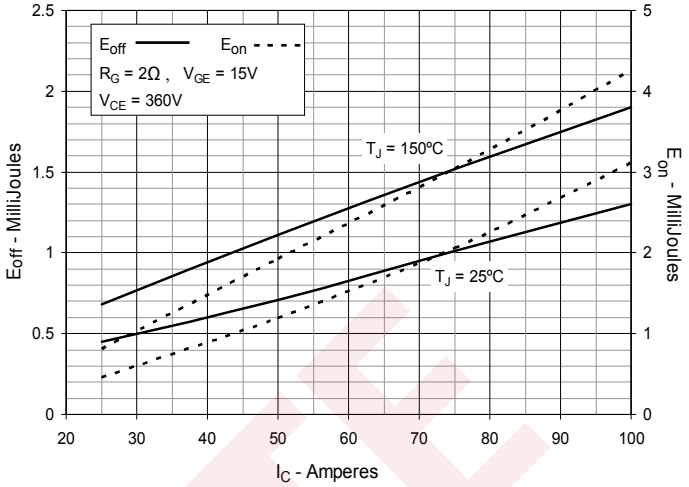


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

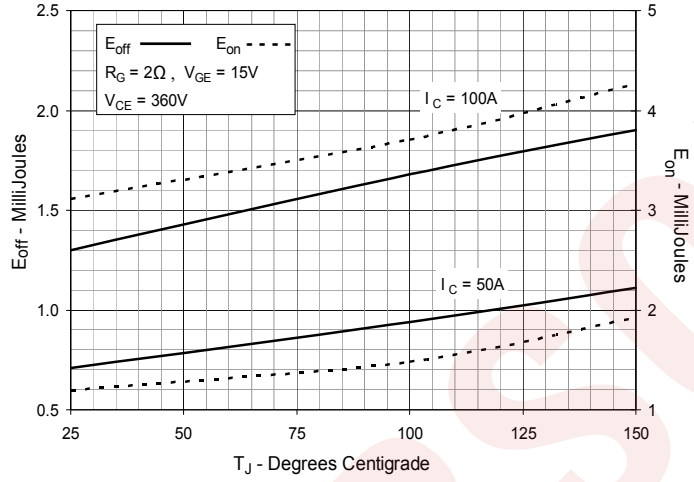


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

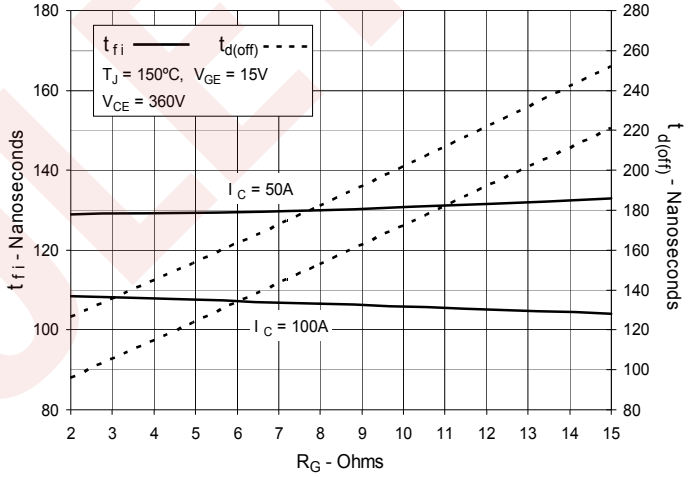


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

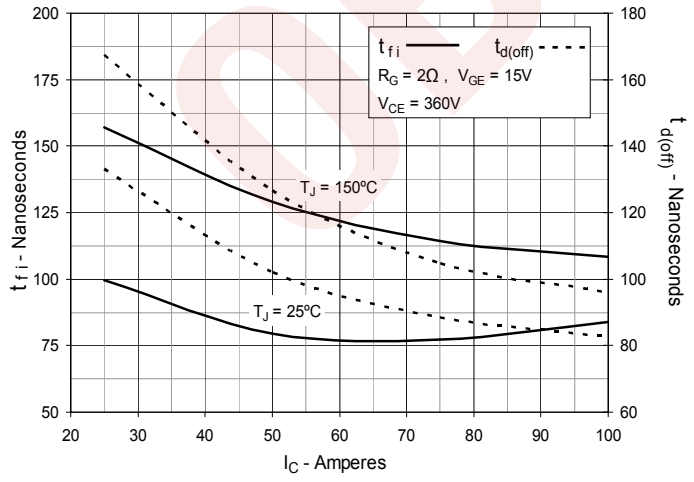
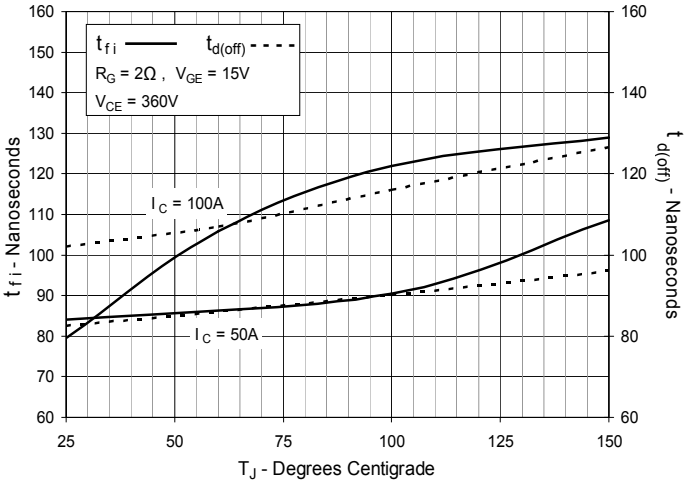


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature



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Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

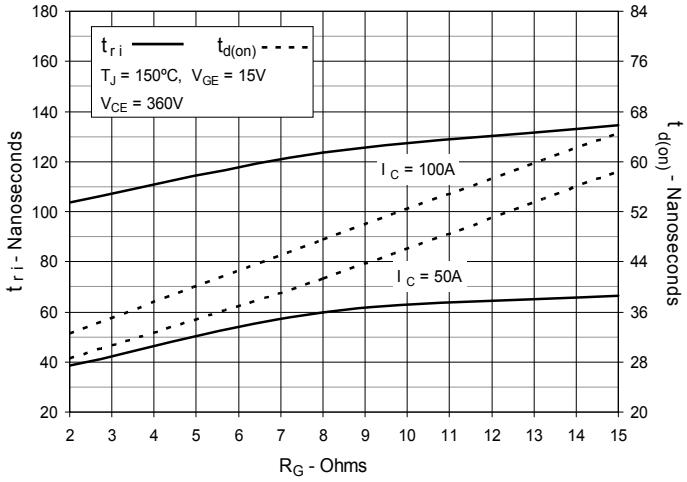


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

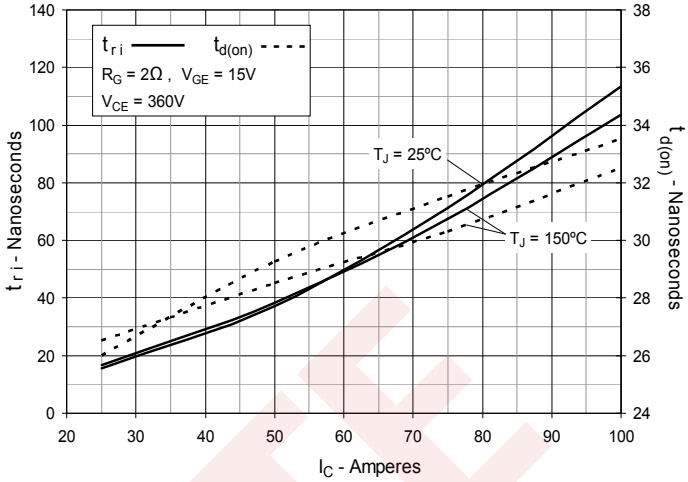
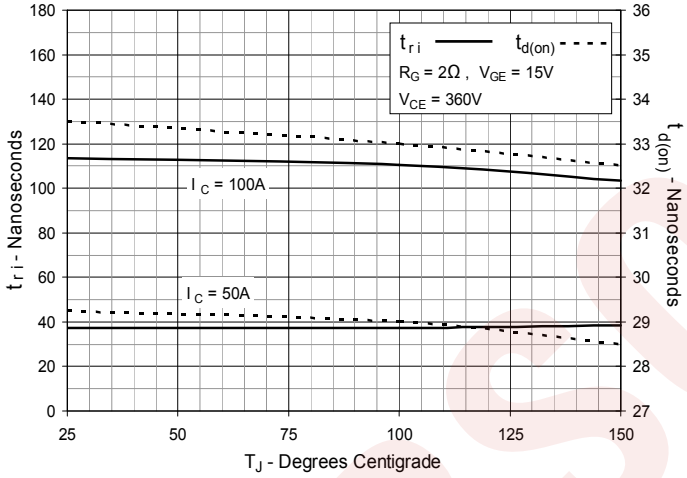


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



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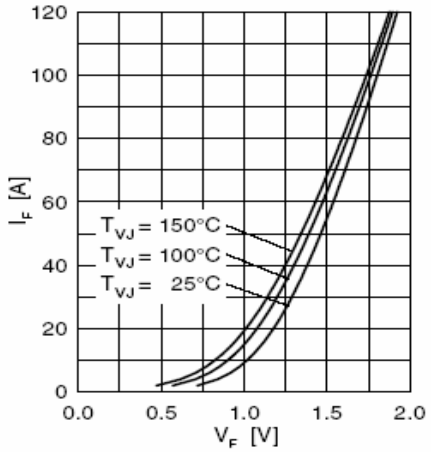


Fig. 22. Forward Current I_F Versus V_F

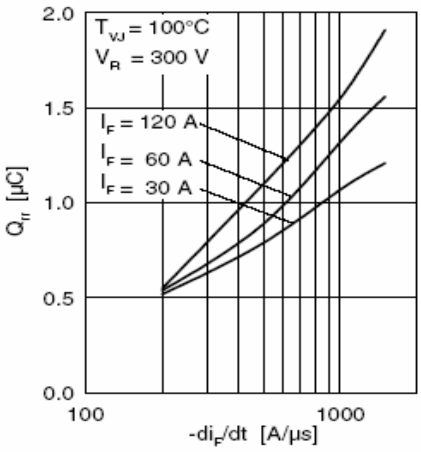


Fig. 23. Reverse Recovery Charge Q_r Versus $-di_F/dt$

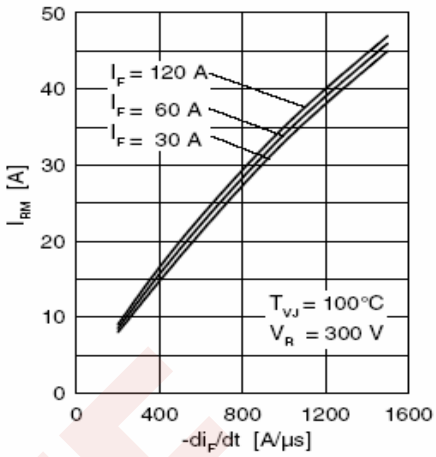


Fig. 24. Peak Reverse Current I_{RM} Versus $-di_F/dt$

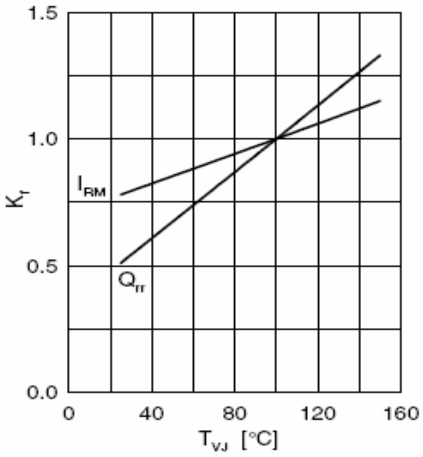


Fig. 25. Dynamic Parameters Q_r, I_{RM} Versus T_{VJ}

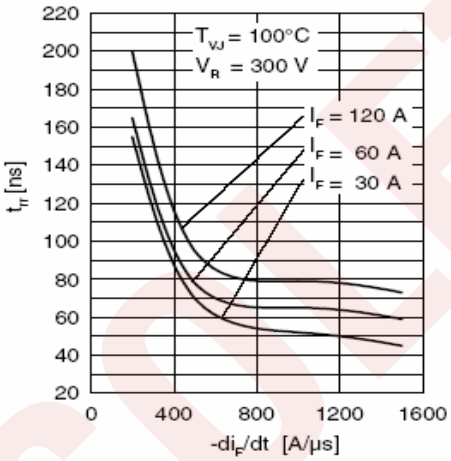


Fig. 26. Recovery Time t_{rr} Versus $-di_F/dt$

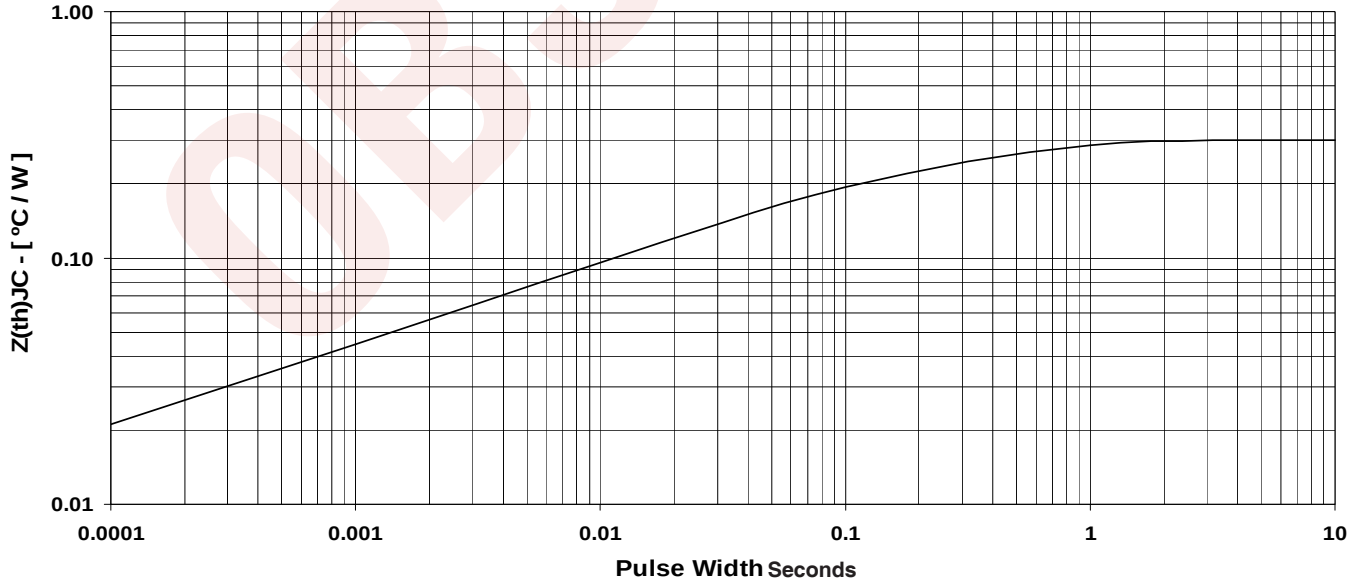


Fig. 27. Maximum transient thermal impedance junction to case (for diode)

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